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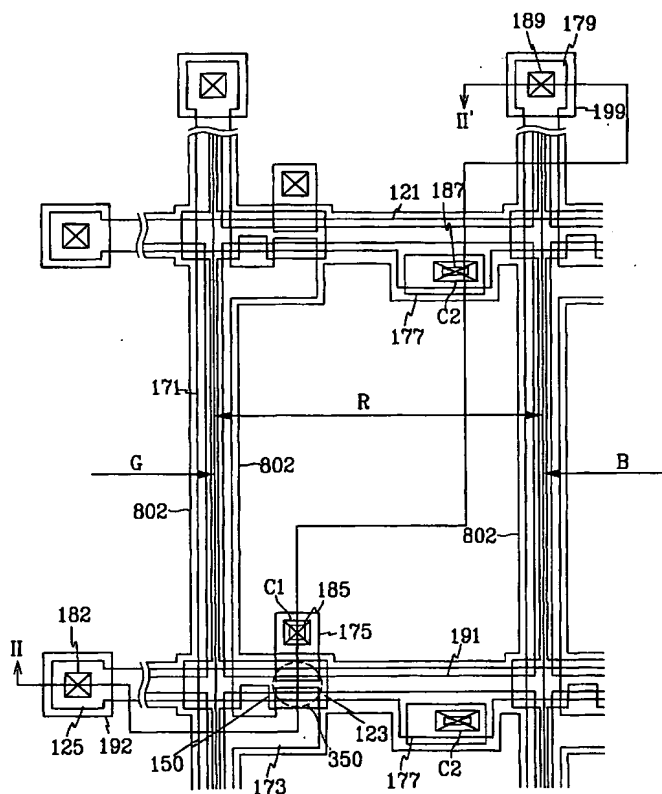
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(54) Title: LIQUID CRYSTAL DISPLAY AND THIN FILM TRANSISTOR ARRAY PANEL THEREFOR



(57) Abstract: A thin film transistor array panel is provided, which includes: a gate line, a gate insulating layer and a semiconductor layer sequentially on a substrate; a data line formed on the gate insulating layer and including a source electrode; a drain electrode formed at least in part on the semiconductor layer; a color filter formed on the data line and the drain electrode and having a first opening exposing the drain electrode at least in part; a light blocking layer formed on the color filter; a passivation layer formed on the color filter and the light blocking layer and having a contact hole exposing the drain electrode through the first opening of the color filter; a pixel electrode formed on the passivation layer and contacting the drain electrode through the contact hole; and a spacer formed on the passivation layer and disposed opposite the light blocking layer.

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